



MGSF1P02LT1 Information



For Reference Only

Part Number MGSF1P02LT1
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 20V 750MA SOT-23

Package TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









MGSF1P02LT1 Specifications

Manufacturer Part Number MGSFIPO2LTI Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 750mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 130pF @ 5V Vgs (Max) ± 20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3 Report errors?		
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Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 750mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 250μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 130pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 750mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 250μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 130pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Package	TO-236-3, SC-59, SOT-23-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C750mA (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.4V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds130pF @ 5VVgs (Max)±20VFET Feature-Power Dissipation (Max)400mW (Ta)Rds On (Max) @ Id, Vgs350 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Series	-
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C750mA (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.4V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds130pF @ 5VVgs (Max)±20VFET Feature-Power Dissipation (Max)400mW (Ta)Rds On (Max) @ Id, Vgs350 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 750mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 250µA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 130pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 4.5V, 10V 2.4V @ 250μA	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 2.4V @ 250μA 2.4V @ 250μA 2.4V @ 250μA 4.00mW (Ta) 130pF @ 5V +20V +20V -50° C ~ 150° C (TJ) Surface Mount Surface Mount Supplier Device Package TO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	750mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 130pF @ 5V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 130pF @ 5V 420V	Vgs(th) (Max) @ Id	2.4V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 350 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	130pF @ 5V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs350 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	400mW (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	350 mOhm @ 1.5A, 10V
Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	SOT-23-3 (TO-236)
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

MGSF1P02LT1 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

MGSF1P02LT1 Payment Methods



















MGSF1P02LT1 Shipping Methods













If you have any question about MGSF1P02LT1, please do not hesitate to contact us!

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